Average gate power dissipation	$P_{G(AV)}$	20	W
Peak gate power dissipation (T_j=25 °C, t_p=8 μs)	V_{FGM}	0.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 °C unless otherwise specified)

Symbol	Test Conditions	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	-	-	20	mA
V_{GT}		-	-	1	V
V_{GD}	V_D=V_{DRM} T_j=125 °C R_L=3.3kΩ	0.2	-	-	V
I_L	I_G=1.2I_{GT}	-	-	70	mA
I_H	I_T=500mA	-	-	60	mA
dV/dt	V_D=540V Gate open T_j=125 °C	1000	-	-	V/μs
t_{gt}	I_G=200mA I_A=200mA I_R=20mA T_j=25 °C	-	2	-	μs
t_{gt}		-	50	-	

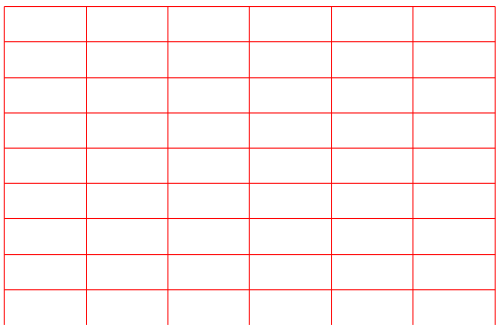
STATIC CHARACTERISTICS

Symbol	Test Conditions		Value (MAX.)	Unit
V_{TM}	I_{TM}=50A t_p=380 μs	T_j=25 °C	1.5	V
V_{to}	Threshold voltage	T_j=125 °C	1	V
R_D	Dynamic resistance	T_j=125 °C	9.3	mΩ
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25 °C	5	μA
I_{RRM}		T_j=125 °C	0.7	mA

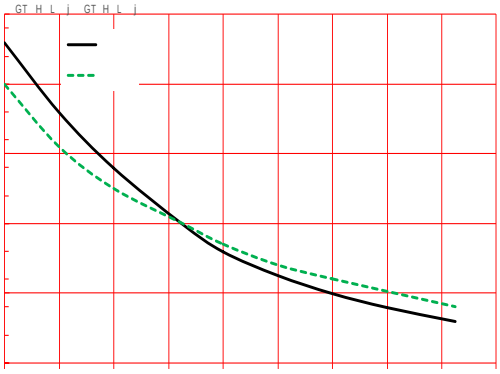
THERMAL RESISTANCES

Symbol	Test Conditions	Value	Unit
$R_{th(j-c)}$	Junction to case (DC)	1	°C/W
$R_{th(j-a)}$	Junction to ambient (1 cm²)	45	°C/W

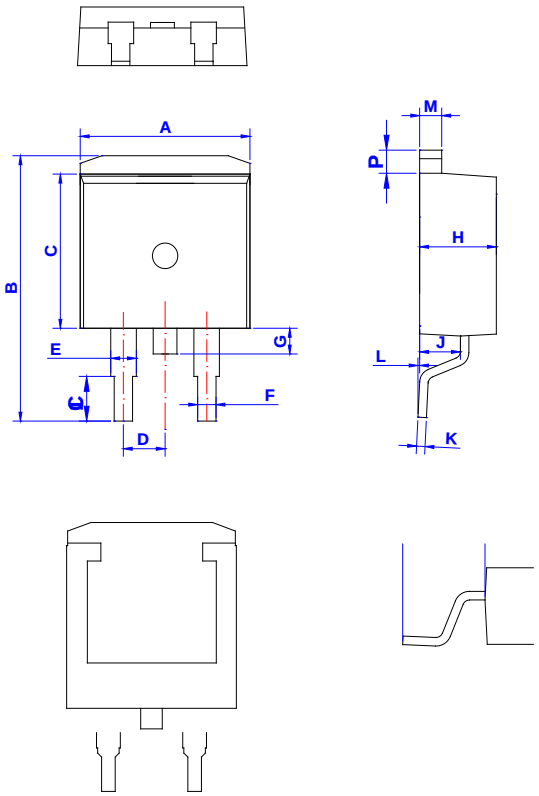
FI : G .1 FI .2:



Fl G .7:



PACKAGE MECHANICAL DATA



R						
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40		2.70	0.094		0.106
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033